



DMG8880LK3

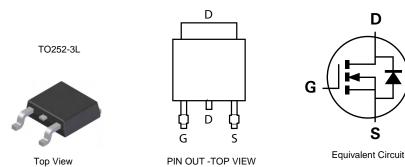
#### N-CHANNEL ENHANCEMENT MODE MOSFET

#### Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: TO252-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.33 grams (approximate)



# Ordering Information (Note 3)

Part Number	Case	Packaging
DMG8880LK3-13	TO252-3L	2500 / Tape & Reel

G8880L = Product Type Marking Code

YYWW = Date Code Marking

YY = Year (ex: 09 = 2009) WW = Week (01 ~ 53)

Notes: 1. No purposefully added lead.

2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.

3. For packaging details, go to our website at http://www.diodes.com.

## **Marking Information**



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DMG8880LK3

Document number: DS32052 Rev. 3 - 2

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### Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 4) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = 25°C T <sub>A</sub> = 85°C	ID	11 8	А
Continuous Drain Current (Note 5) $V_{GS}$ = 10V	Steady State	T <sub>A</sub> = 25°C T <sub>A</sub> = 85°C	ID	16.5 12	А
Pulsed Drain Current (Note 6)		•	I <sub>DM</sub>	48	А

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	PD	1.68	W
Thermal Resistance, Junction to Ambient $@T_A = 25^{\circ}C$ (Note 4)	R <sub>0JA</sub>	74.3	°C/W
Power Dissipation (Note 5)	PD	4.1	W
Thermal Resistance, Junction to Ambient $@T_A = 25^{\circ}C$ (Note 5)	R <sub>0JA</sub>	30.8	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

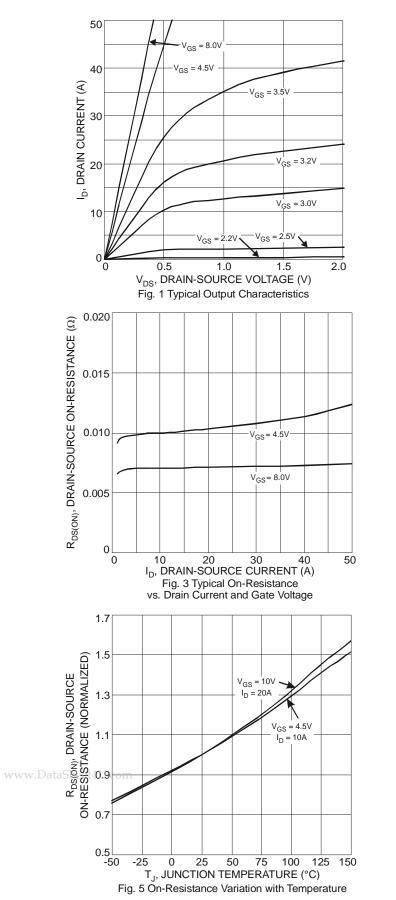
## Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

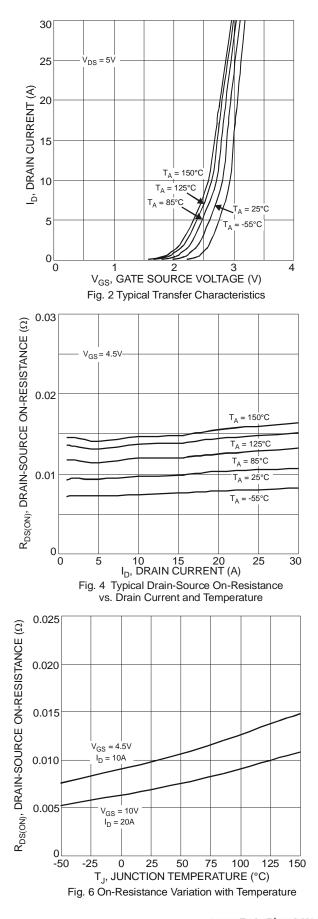
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)						•	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current TJ = 25°C	IDSS	-	-	1.0	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	1.5	2.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance			7.0	9.3	mΩ	$V_{GS} = 10V, I_D = 11.6A$	
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)	-	9.6	14	111.2.2	$V_{GS} = 4.5V, I_D = 10.7A$	
Forward Transfer Admittance	Y <sub>fs</sub>	-	22	-	S	V <sub>DS</sub> = 15V, I <sub>D</sub> = 15A	
Diode Forward Voltage	V <sub>SD</sub>	-	0.7	1.0	V	$V_{GS} = 0V, I_{SD} = 2.1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	-	1289	-	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Output Capacitance	C <sub>oss</sub>	-	187	-	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	-	162	-	рF	1 = 1.00012	
Gate Resistance	Rg	-	0.97	-	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge at 10V	Qg	-	27.6	-	nC	$V_{GS} = 10V, V_{DS} = 15V,$ $I_D = 11.6A, Ig = 1.0mA$	
Total Gate Charge at 5V	Qg	-	14.4	-	nC	$-V_{GS} = 5V, V_{DS} = 15V,$ $-I_D = 11.6A$	
Gate-Source Charge	Q <sub>gs</sub>	-	3.6	-	nC		
Gate-Drain Charge	Q <sub>gd</sub>	-	4.9	-	nC		
Turn-On Delay Time	t <sub>D(on)</sub>	-	7.04	-	ns	$V_{DD} = 15V, V_{GS} = 10V, \\ R_G = 11\Omega, I_D = 11.6A, \\ R_L = 1.3\Omega$	
Turn-On Rise Time	tr	-	17.52	-	ns		
Turn-Off Delay Time	t <sub>D(off)</sub>	-	36.13	-	ns		
Turn-Off Fall Time	tf	-	19.67	-	ns		

 Device mounted on FR-4 PCB, with minimum recommended pad layout, single sided.
Device mounted on 2" x 2" FR-4 PCB with high coverage 2oz. copper, single sided.
Repetitive rating, pulse width limited by junction temperature and current limited by package.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to production testing. Notes:

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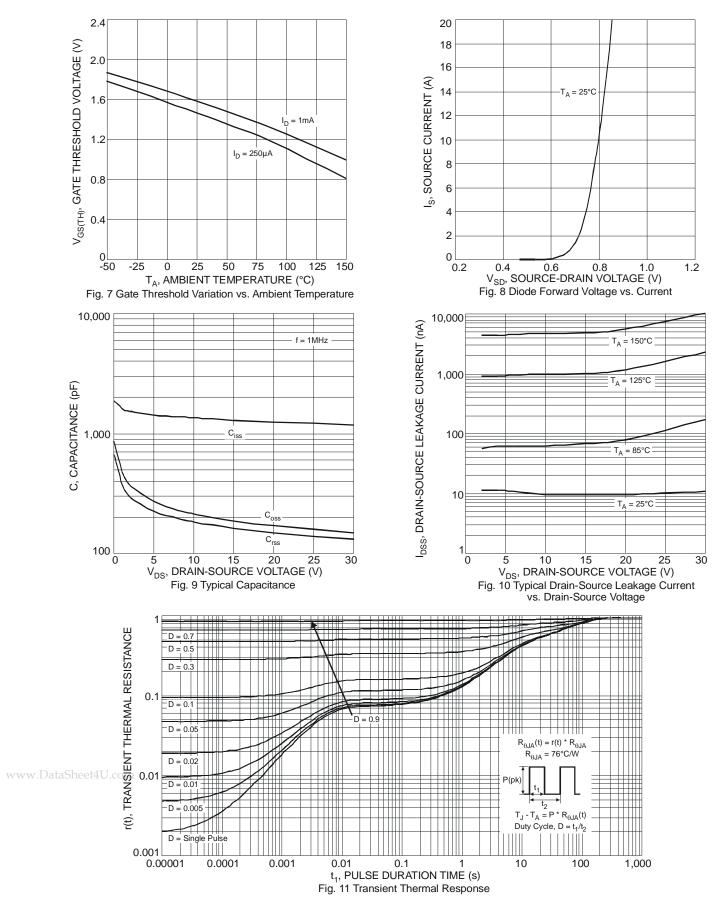






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Max

2.39

1.17

0.88

1.14

5.50

0.58

6.20

6.70

10.41

1.78

1.27

1.02

10°

2.29

1.07

0.76

0.95

5.33

0.51

6.10

6.58

9.91

1.59

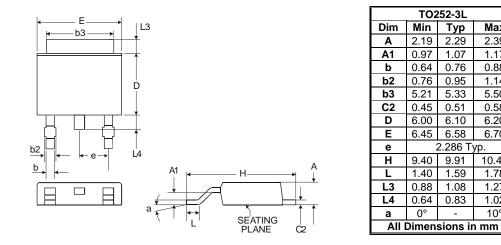
1.08

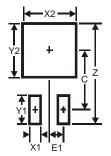
0.83

-

2.286 Тур

# **Package Outline Dimensions**





Dimensions	Value (in mm)
Z	11.6
X1	1.5
X2	7.0
Y1	2.5
Y2	7.0
C	6.9
E1	2.3



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